



Bipolar NPN Bare Die – BTN6012

Part Description

The BTN6012 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. PNP Complement is BTP6012.

Key Parameters:

- VCBO = 80V
- VCEO = 60V
- VEBO = 5V
- hFE = 100- @ VCE = 5V, IC = 1A
- VCE(Sat) = 0.28V @ IC = 1A, IB = 100mA
- fT = 150 MHz @ VCE = 10V, IE = 0A
- COBO = 10pF @ VCB = 10V

Features

Very Low VCE(sat). Designed to provide performance equivalent to NXP / NEXPERIA PBSS4160U

Die Size (Unawn)

660µm X 660µm, 26 Mils X 26 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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